

1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- · Triggering in three quadrants only

3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DRM}	repetitive peak off- state voltage			-	-	600	V	
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5		-	-	100	Α	
I _{T(RMS)}	RMS on-state current	full sine wave; $T_h \le 59$ °C; Fig. 1; Fig. 2; Fig. 3		-	-	12	А	
Static characte	Static characteristics							
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	10	mA	





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	10	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		sym051
3	G	gate		·
mb	n.c.	mounting base; isolated		
			TO-220F (SOT186A)	

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BTA312X-600E	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A				
BTA312X-600E/DG	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack"	SOT186A				

7. Marking

Table 4. Marking codes

Type number	Marking code
BTA312X-600E	
BTA312X-600E/DG	BTA312X-600EDG

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{DRM}	repetitive peak off-state voltage		-	600	V	
I _{T(RMS)}	RMS on-state current	S on-state current full sine wave; $T_h \le 59$ °C; Fig. 1; Fig. 2; Fig. 3				
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	100	A	
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	110	A	
l ² t	I ² t for fusing	t_p = 10 ms; SIN	-	50	A ² s	
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs	
I _{GM}	peak gate current		-	2	Α	
P_GM	peak gate power		-	5	W	
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W	
T _{stg}	storage temperature		-40	150	°C	
Tj	junction temperature		-	125	°C	

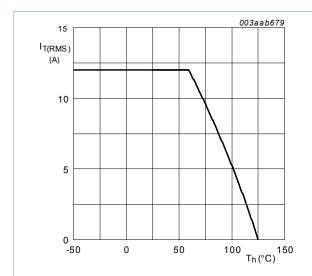


Fig. 1. RMS on-state current as a function of heatsink temperature; maximum values

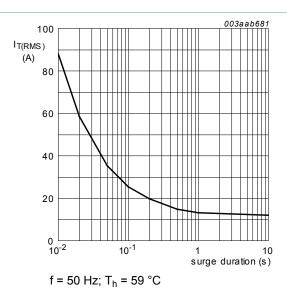
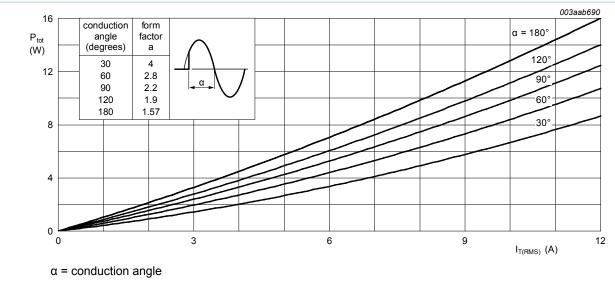


Fig. 2. RMS on-state current as a function of surge duration; maximum values

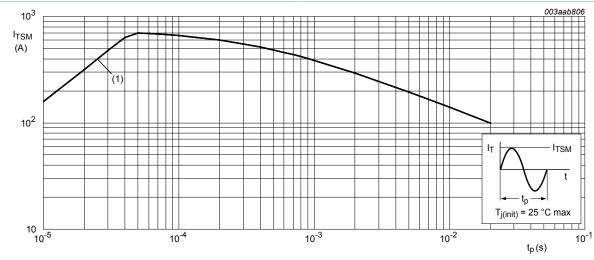
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3Q Hi-Com Triac



a = form factor = $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms}$

(1) dl_T/dt limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values

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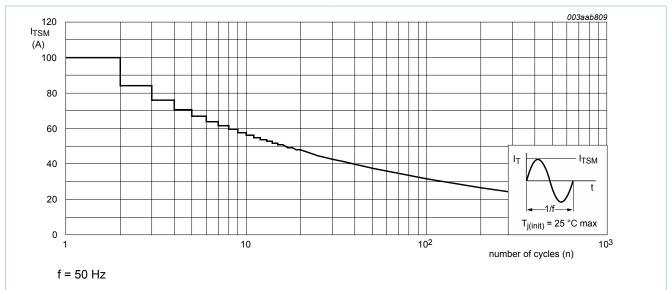
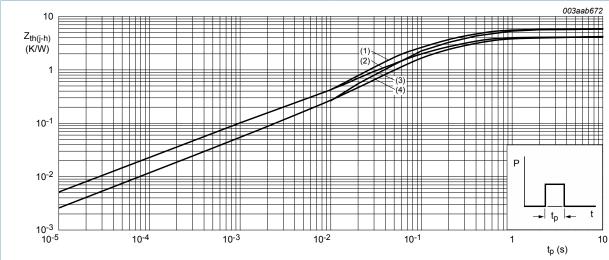


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$\begin{array}{c} R_{th(j\text{-}h)} & \text{thermal resistance} \\ \text{from junction to} \end{array}$						4	K/W
heatsink	full cycle or half cycle; without heatsink compound; Fig. 6		-	-	5.5	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		_	55	-	K/W



- (1) Unidirectional (half cycle) without heatsink compound
- (2) Unidirectional (half cycle) with heatsink compound
- (3) Bidirectional (full cycle) without heatsink compound
- (4) Bidirectional (full cycle) with heatsink compound

Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse duration

10. Isolation characteristics

Table 7. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _h = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; f = 1 MHz; T _h = 25 °C	-	10	-	pF

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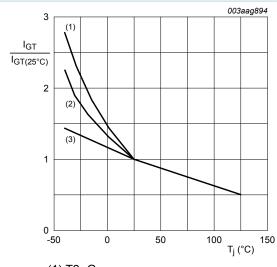
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11. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	10	mA
I _L latching current		latching current $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$				
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 8$		-	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V_{GT}	gate trigger voltage	gate trigger voltage $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11		0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		,			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 61 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	50	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	3	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 12 \text{ A};$ $dV_{com}/dt = 10 \text{ V/}\mu\text{s}; gate open circuit}$	6	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 12 A; dV_{com}/dt = 1 V/ μ s; gate open circuit	10	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

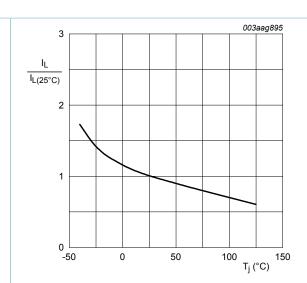


Fig. 8. Normalized latching current as a function of junction temperature

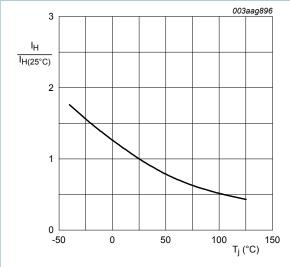
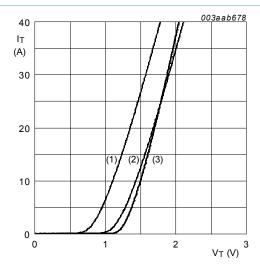


Fig. 9. Normalized holding current as a function of junction temperature



 $V_0 = 1.164 \text{ V}; R_s = 0.027 \Omega$

(1) T_j = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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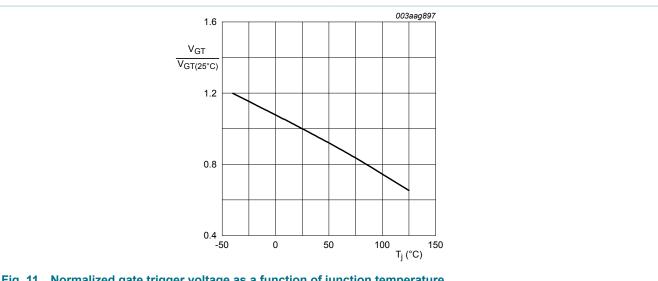
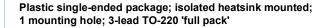
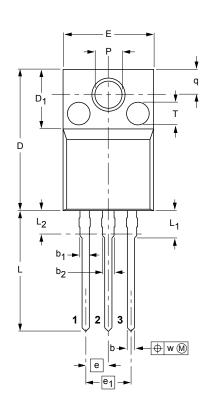


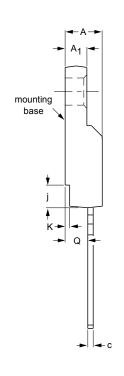
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

12. Package outline



SOT186A





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁	b ₂	С	D	D ₁	E	е	e ₁	j	К	L	L ₁	L ₂ ⁽¹⁾ max.	Р	Q	q	T ⁽²⁾	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	1.4 1.0	0.7 0.4	15.8 15.2	6.5 6.3	10.3 9.7	2.54	5.08	2.7 1.7	0.6 0.4	14.4 13.5	3.30 2.79	3	3.2 3.0	2.6 2.3	3.0 2.6	2.5	0.4

Notes

- 1. Terminal dimensions within this zone are uncontrolled.
- 2. Both recesses are # 2.5×0.8 max. depth

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA	PROJECTION		ISSUE DATE
SOT186A		3-lead TO-220F				-02-04-09 06-02-14

Fig. 12. Package outline TO-220F (SOT186A)

BTA312X-600E

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